## NSN 5961-00-179-4447

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Inclosure Material:
Metal
Overall Length:
0.400 inches
Overall Diameter:
0.424 inches
Mounting Facility Quantity:
1
Mounting Method:
Threaded stud
Thread Size:
0.190 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
400.0 reverse voltage, peak
Current Rating Per Characteristic:
4.70 amperes zero-gate-voltage source current preset and 60.00 amperes forward current, total rms watts
Power Rating Per Characteristic:
0.5 watts small-signal input power, common-collector blank
Maximum Operating Tempurature Per Measurement Point:
105.0 degrees celsius case
Special Features:
Internal junction configuration, pnpn
Thread Series Designator:
Unf
Terminal Type And Quantity:
3 tab, solder lug
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No
Fiig:
A110a0